

SML400HB01MF

- Attributes:
- aerospace build standard
 - high reliability
 - lightweight
 - metal matrix base plate
 - AlN isolation
 - Mosfet module



Maximum rated values/Electrical Properties

Source-drain voltage V_{DSS}	$T_j=25C$ to $175C$ $R_{gs}=1M\Omega$	V_{DSS}	100	V
DC Collector Current I_{D25}	$T_c=25C$ $T_c=25C, T_{vj}=175C$	$I_{c, nom}$ I_c	400 400	A
Repetitive peak Drain Current	$t_p=1msec, T_c=80C$	I_{crm}	600	A
Total Power Dissipation	$T_c=25C$	P_{tot}	1700	W
Gate-emitter peak voltage	Continuous Transient	V_{GS}	+/-20 =/-30	V V
Repetitive Peak Forward Current	$t_p=1msec$	I_{frm}	600	A
Isolation voltage	RMS, 50Hz, $t=1min$	V_{isol}	2500	V

		MIN		TYP	MAX	
Drain-source breakdown voltage	$I_D=250\mu A, V_{GS}=0V, T_c=25C$	BV_{DSS}	100			V
Gate Threshold voltage	$I_D=8mA, V_{DS}=V_{GS}, T_{vj}=25C$	$V_{ge(th)}$	3.0		5	V
<div><div>C_{iss}</div><div>C_{oss}</div><div>C_{rss}</div></div>	$f=1MHz, T_{vj}=25C, V_{gs}=0V, V_{DS}=0V$			15200		pF
				5800		pF
				1720		pF
<div><div>$Q_{g(on)}$</div><div>Q_{gs}</div><div>Q_{gd}</div></div>	$T_{vj}=25C, V_{DS}=0.5V_{DSS}, I_D=0.5I_{D25}, V_{GS}=10V$			470		nC
				100		nC
				270		nC
Gate-source leakage current	$V_{GS}=+/-20V, V_{GS}=0V, T_{vj}=25C$	I_{GSS}		1	+/-200	nA
Drain source leakage current	$V_{DS}=V_{GS}=20V, T_{vj}=25C$ $T_{vj}=150C$ $T_{vj}=175C$	I_{DSS}			25 1 5	μA mA mA

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders



gfs	V _{GS} =10V, I _D =0.5I _{D25}		60	97		S
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	I _C =120A, V _{DS} =0.5V _{DSS} , V _{GS} =10V R _{ge} =3.3Ω, L=30nH T _{vj} =25C			50 60 150 90		ns ns Ns ns
Stray Module inductance		L _{σce}		30		nH
Terminal-chip resistance		R _c		1.0		mΩ

Source –Drain Diode characteristics

TYP MAX

DC Forward Diode Current I _s	T _c =25C V _{GS} =0V	I _s		400	A
Repetitive forward current		I _{sm}		800	A
	I _F =I _s , V _{GS} =0V t _p =300μsec, duty cycle=2%	V _{SD}		1.5	V
Peak reverse recovery current	I _F =50A, -di/dt=100A/μsec V _R =50V, V _{GS} =0V, T _{vj} =25C	I _{rm}	12		A
Reverse recovery time	I _F =50A, -di/dt=100A/μsec V _R =50V, V _{GS} =0V, T _{vj} =25C	t _{rr}		300	ns
Recovered charge	I _F =50A, -di/dt=100A/μsec V _R =50V, V _{GS} =0V, T _{vj} =25C	Q _{rm}	0.8		μC



Thermal Properties

			Min	Typ	Max	
Thermal resistance junction to case	Igibt Diode	$R_{\theta J-C}$			0.09 0.11	K/W
Thermal resistance case to heatsink		$R_{\theta C-hs}$		0.03		K/W
Maximum junction temperature		T_{vj}			175	C
Maximum operating temperature		T_{op}	-55		175	C
Storage Temperature		T_{stg}	-55		175	C

Fig. 1. Output Characteristics
@ 25°C

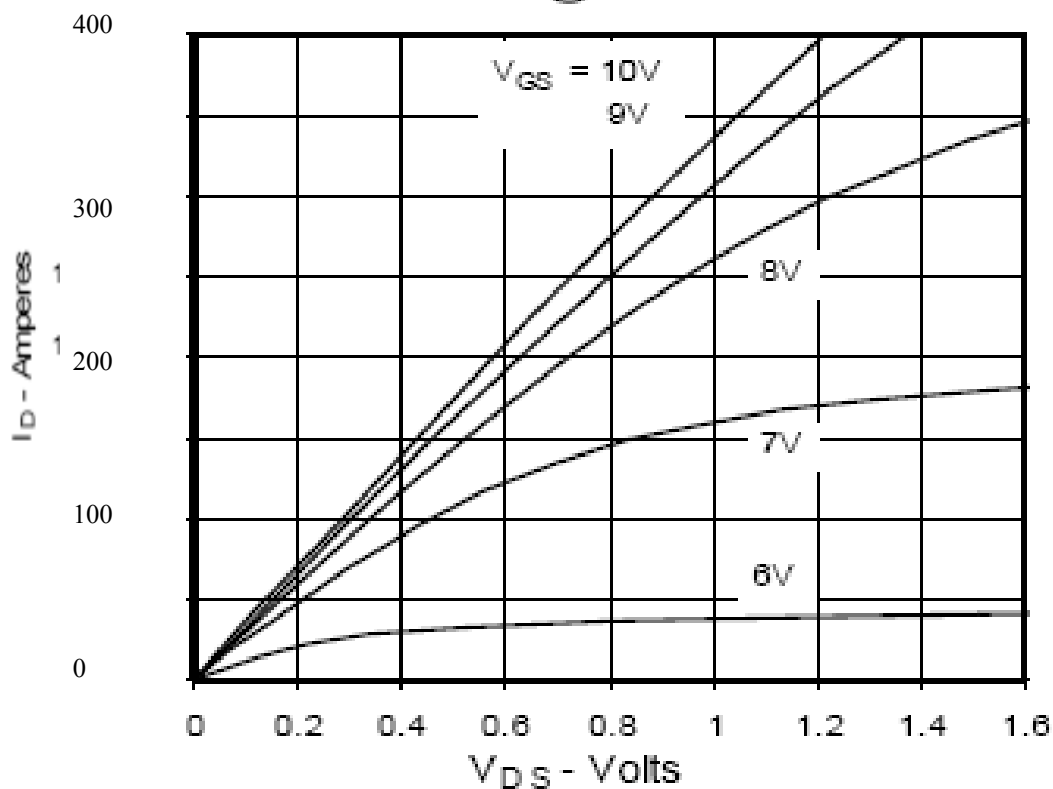


Fig. 2. Extended Output Characteristics
@ 25°C

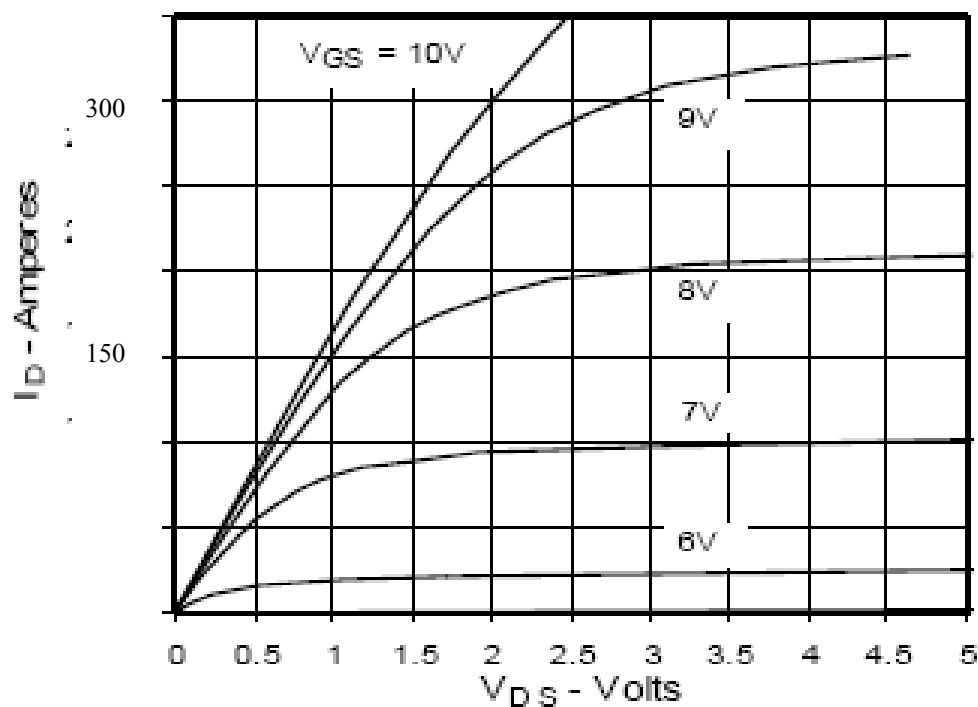


Fig. 3. Output Characteristics
@ 150°C

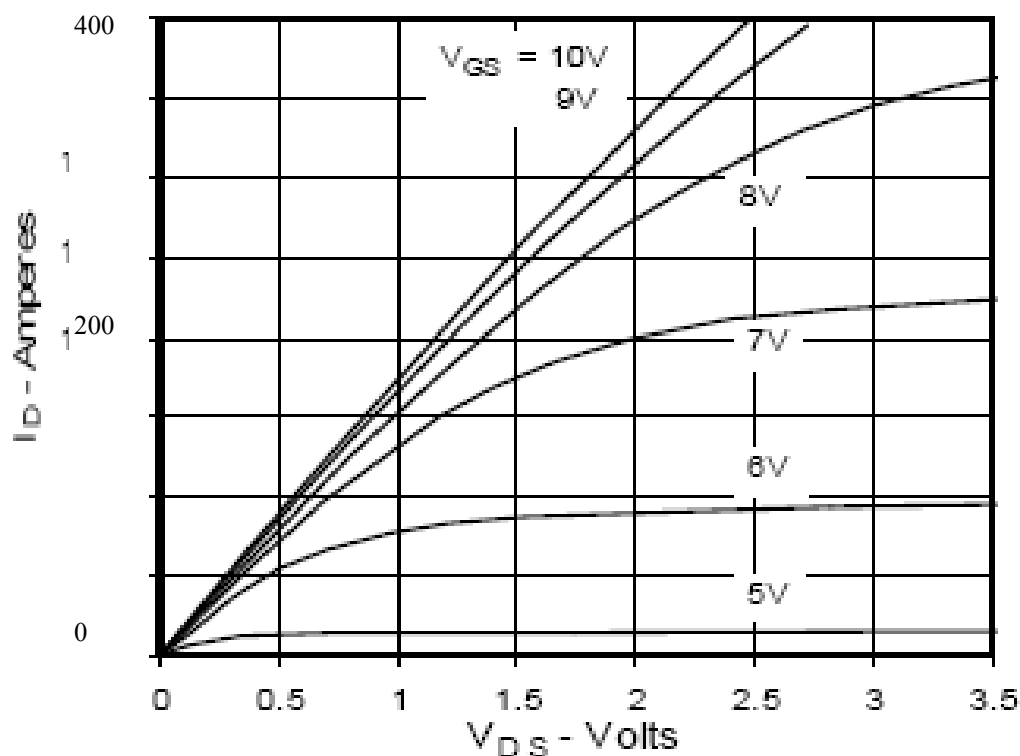


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

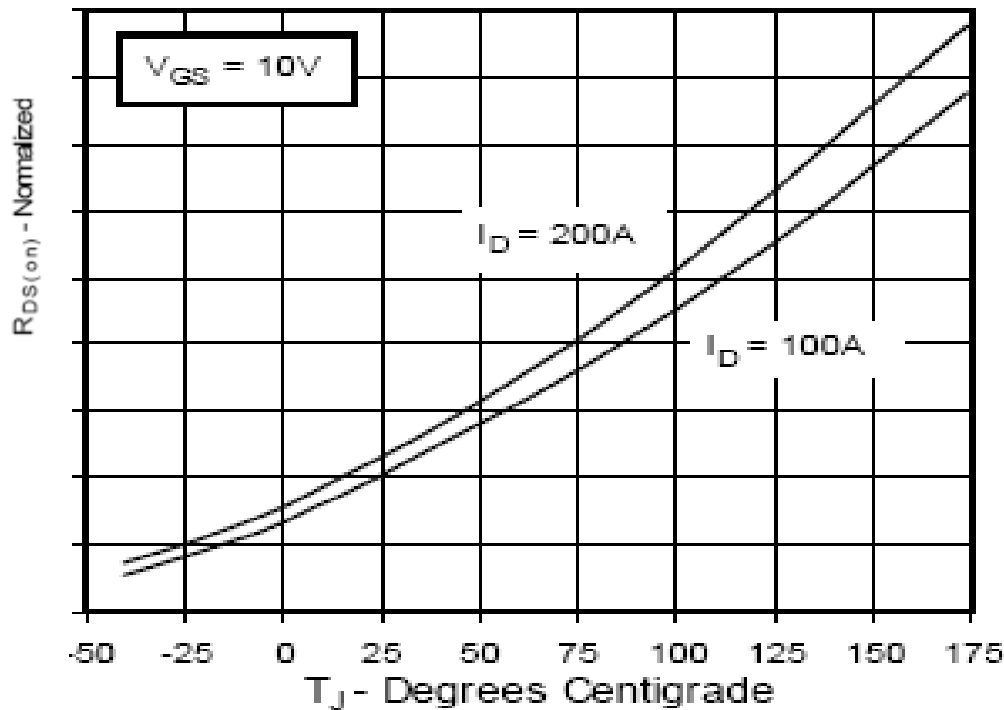


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Drain Current

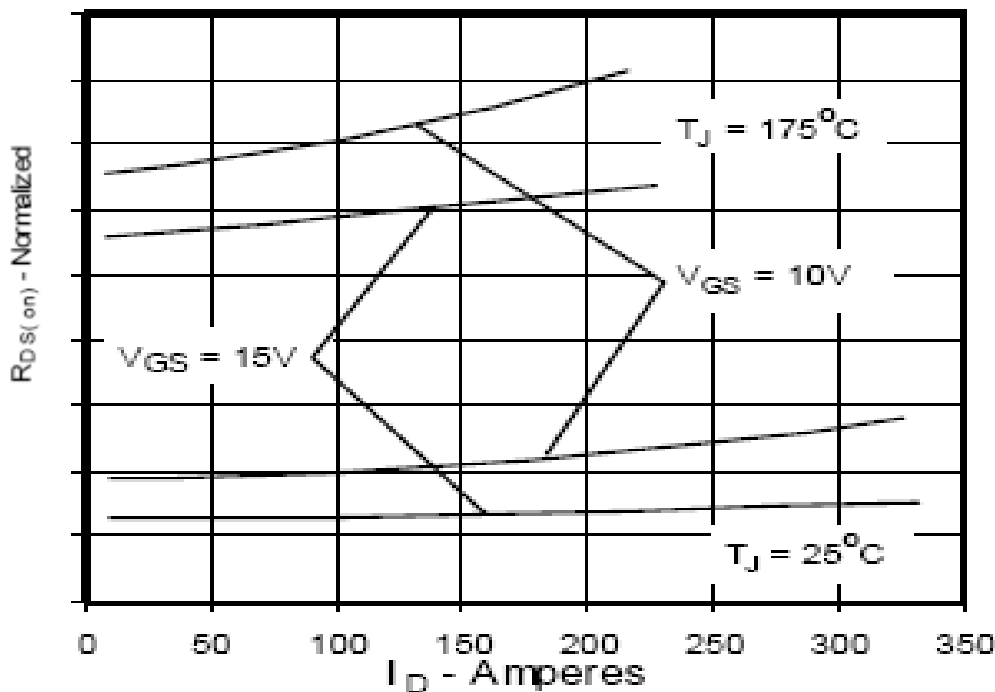


Fig. 6. Drain Current vs. Case Temperature

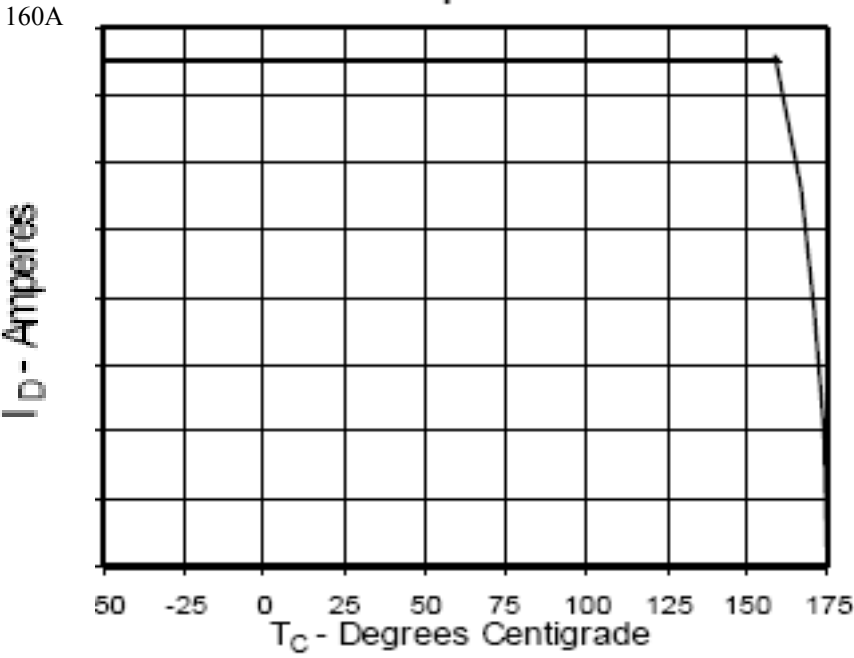


Fig. 7. Input Admittance

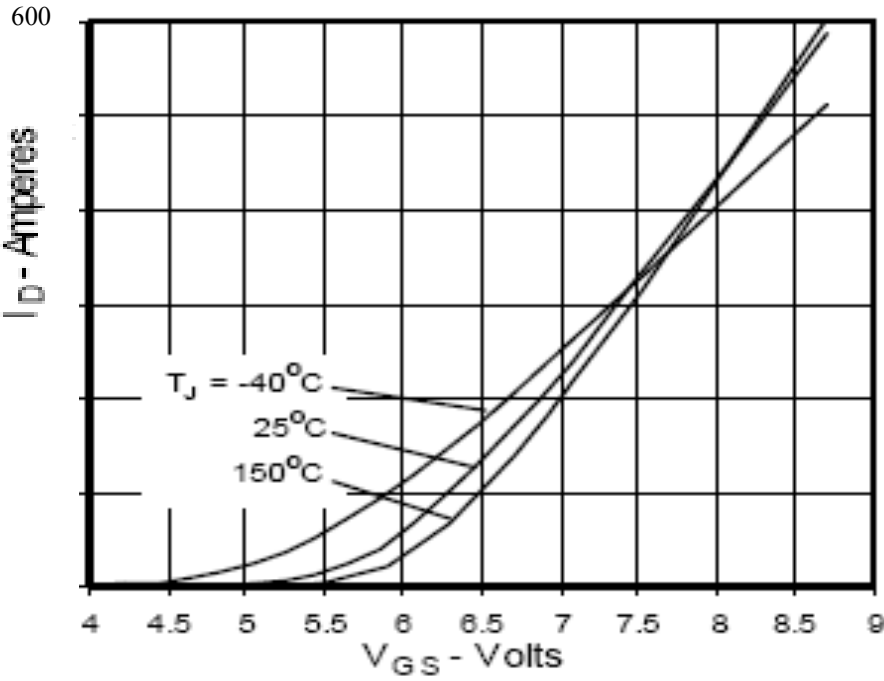


Fig. 8. Trans conductance

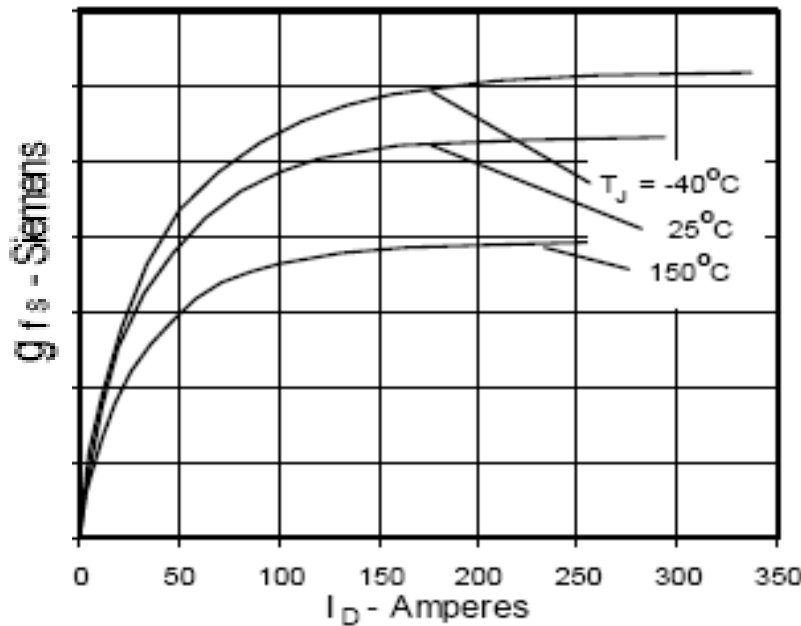


Fig. 9. Source Current vs. Source-To-Drain Voltage

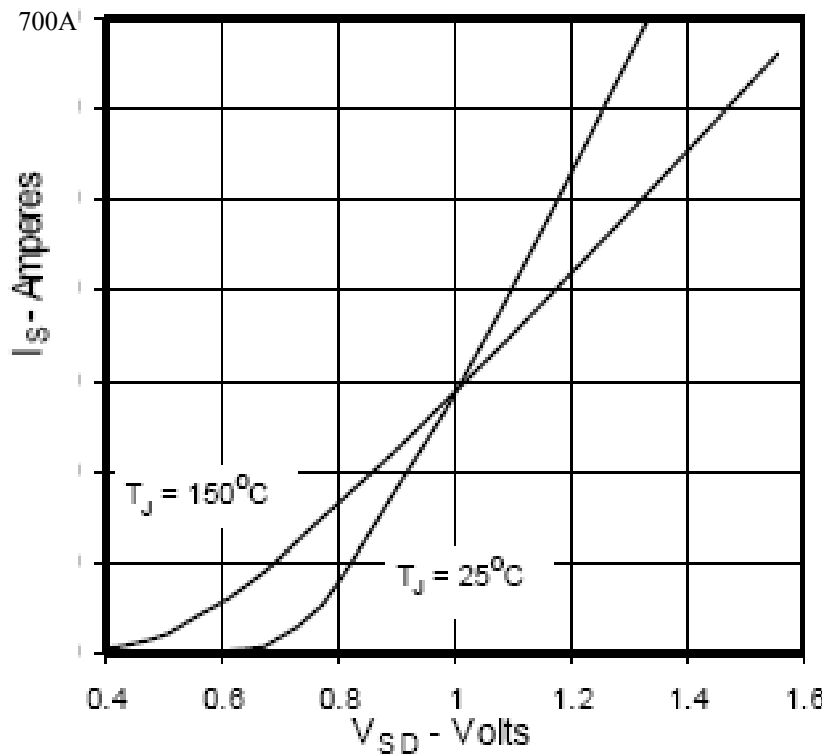




Fig. 10. Gate Charge

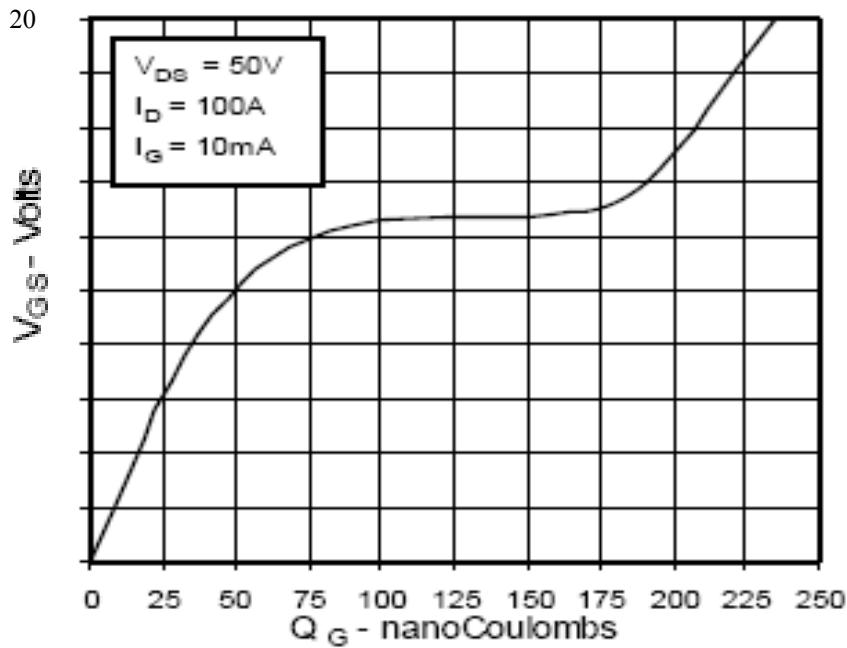
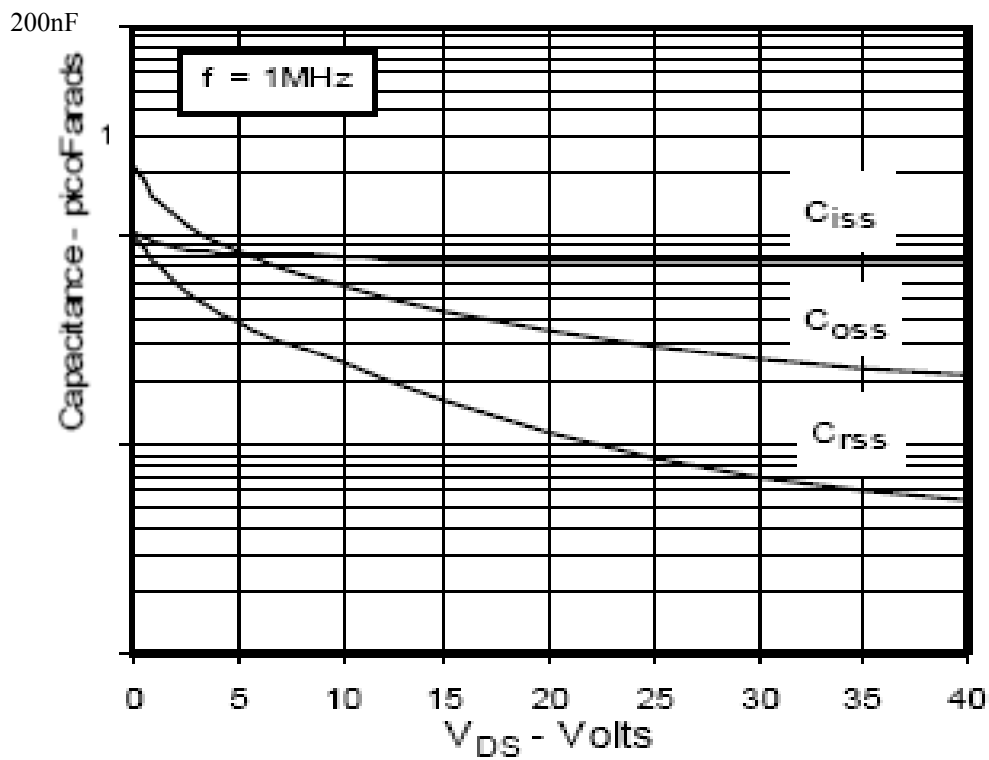
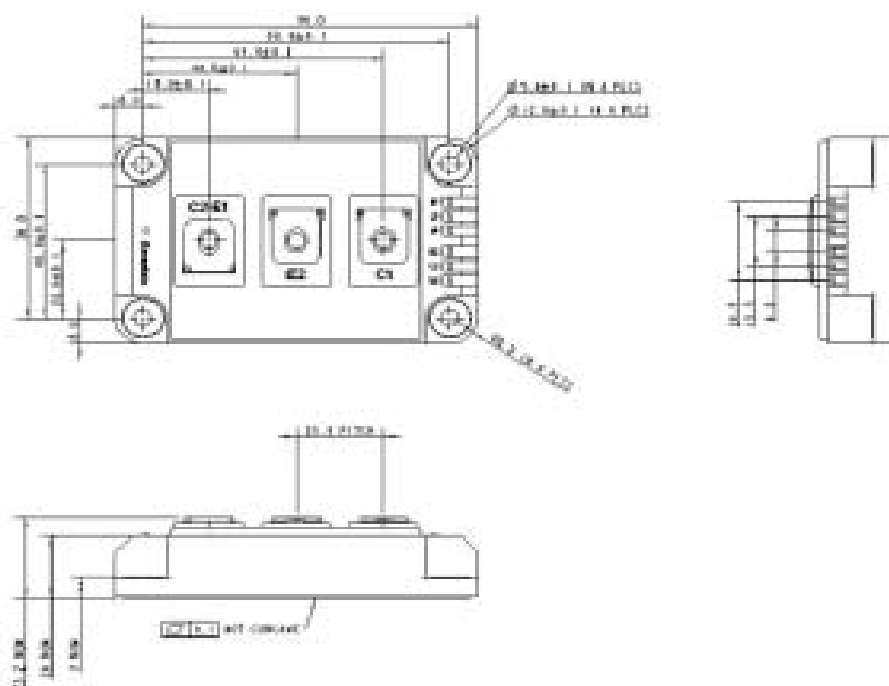
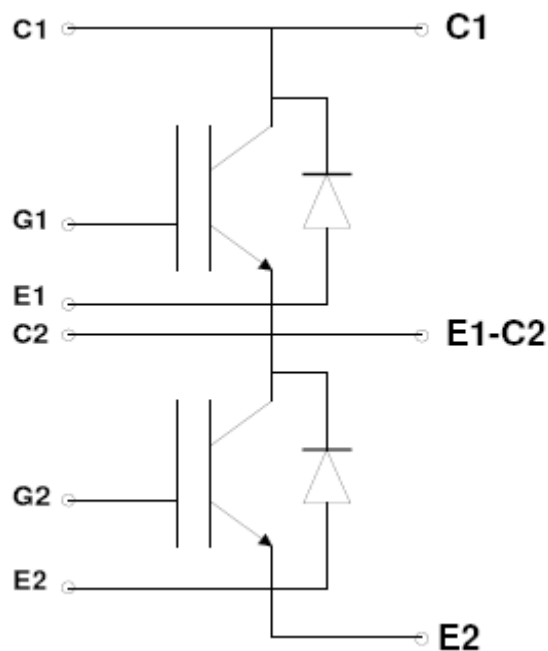


Fig. 11. Capacitance





All dimensions in mm



CIRCUIT DIAGRAM